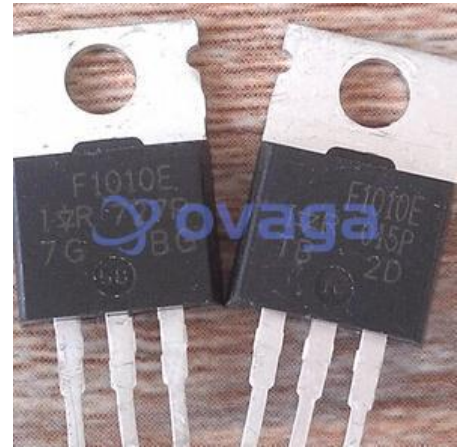


MOSFET, Power; N-Ch; VDSS 60V; RDS(ON) 12 Milliohms; ID 84A; TO-220AB; PD 200W; gFS 69S

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-220AB
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

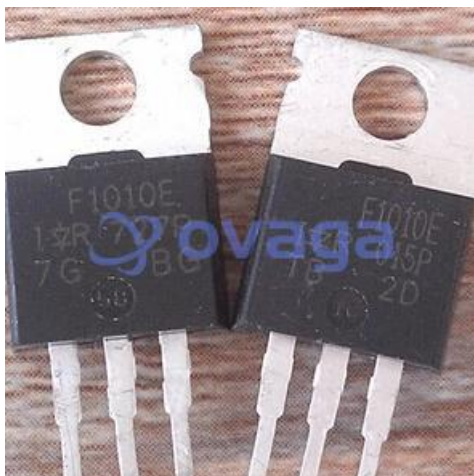
Please submit RFQ for IRF1010EPBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

AUTOMOTIVE MOSFET

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

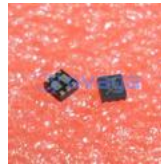


Related Products



[IRLTS6342TRPBF](#)

Infineon Technologies Corporation
TSOP-6



[IRLHS6376TRPBF](#)

Infineon Technologies Corporation
PQFN2x2DD



[IRF9310PBF](#)

Infineon Technologies Corporation
SOIC-8



[IRFH9310TRPBF](#)

Infineon Technologies Corporation
PQFN-8



[IRF9358TRPBF](#)

Infineon Technologies Corporation
SOP-8



[IRFB7430PBF](#)

Infineon Technologies Corporation
TO-220



[IRFB3307ZPBF](#)

Infineon Technologies Corporation
TO-220AB



[IRF7351TRPBF](#)

Infineon Technologies Corporation
SOIC-8